

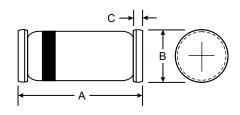
SURFACE MOUNT FAST SWITCHING DIODE

Features

- Ideal for Fast Logic Applications
- Ultra Fast Switching
- High Reliability
- High Conductance

Mechanical Data

- Case: MiniMELF, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Marking: Cathode Band Only
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



MiniMELF						
Dim	Min	Max				
Α	3.30	3.70				
В	1.30	1.60				
С	0.28	0.50				
All Dimensions in mm						

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	LL4150	Unit	
Non-Repetitive Peak Reverse Voltage @ 5.0µA	V _{RM}	V		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	V	
RMS Reverse Voltage	V _{R(RMS)}	35	V	
Forward Continuous Current (Note 1)	I _{FM}	400	mA	
Average Rectified Output Current (Note 1)	lo	200	mA	
Repetitive Peak Forward Current (Note 1)	I _{FRM}	600	mA	
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	IFSM	1.0 4.0	A	
Power Dissipation (Note 1)	Pd	500	mW	
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	300	K/W	
Operating and Storage Temperature Range	Tj, T _{STG}	-65 to +200	°C	

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage Drop	V _{FM}	0.54 0.66 0.76 0.82 0.87	0.62 0.74 0.86 0.92 1.00	V	
Maximum Peak Reverse Current	I _{RM}	_	100	nA μA	$\begin{array}{rl} T_A = & 25^{\circ}C \\ T_A = & 150^{\circ}C \end{array}$
Junction Capacitance	Cj		2.5	pF	V _R = 0V, f = 1.0MHz
Reverse Recovery Time	t _{rr}		4.0	ns	$I_{F} = I_{R} = 200 \text{mA},$ $I_{rr} = 0.1 \text{ x } I_{R}, R_{L} = 100 \Omega$
Forward Recovery Time	t _{fr}		10	ns	I _F = 200mA, V _{FR} = 1.0V

Note: 1. Valid provided that electrodes are kept at ambient temperature.